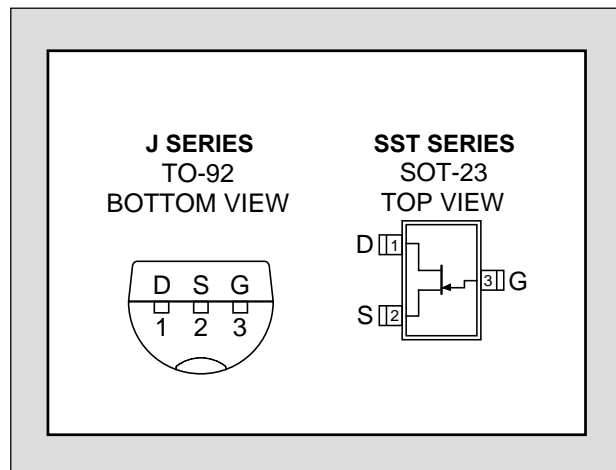


## J/SST201 SERIES

**HIGH GAIN  
N-CHANNEL JFET**

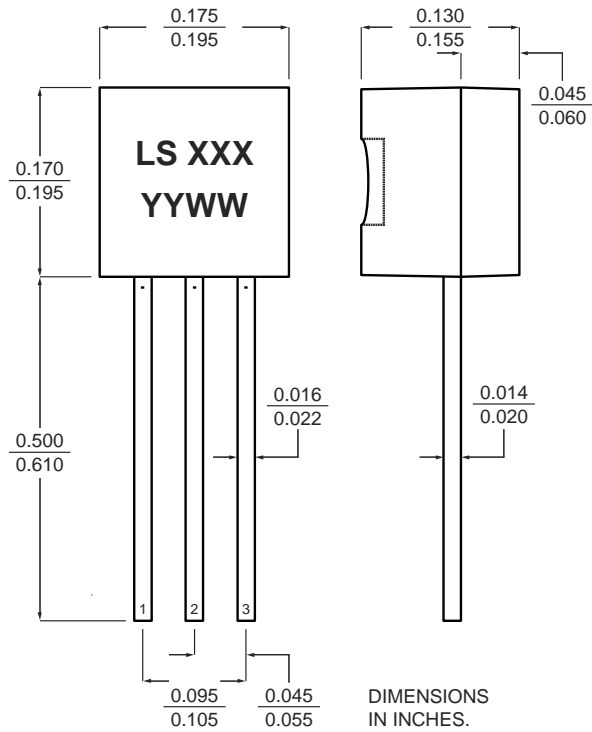
FEATURES	
DIRECT REPLACEMENT FOR SILICONIX J/SST201 SERIES	
LOW CUTOFF VOLTAGE	$V_{GS(off)} \leq 1.5V$
HIGH GAIN	$A_V = 80 V/V$
ABSOLUTE MAXIMUM RATINGS <sup>1</sup>	
@ 25 °C (unless otherwise stated)	
Maximum Temperatures	
Storage Temperature	-65 to +150 °C
Operating Junction Temperature	-55 to +135 °C
Maximum Power Dissipation	
Continuous Power Dissipation	350mW
Maximum Current	
Forward Gate Current	50mA
Maximum Voltages	
Gate to Drain Voltage	-40V
Gate to Source Voltage	-40V



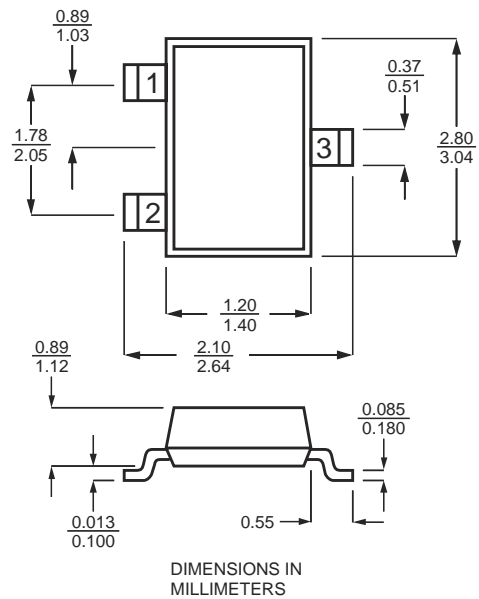
### ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
$BV_{GSS}$	Gate to Source Breakdown Voltage	J/SST201, 202	-40		V	$I_G = -1\mu A, V_{DS} = 0V$
		J/SST204	-25			
$V_{GS(off)}$	Gate to Source Cutoff Voltage	J/SST201	-0.3	-1.5		$V_{DS} = 15V, I_D = 10nA$
		J/SST202	-0.8	-4		
		J/SST204	-0.3	2		
$I_{DSS}$	Drain to Source Saturation Current <sup>2</sup>	J/SST201	0.2	1	mA	$V_{DS} = 15V, V_{GS} = 0V$
		J/SST202	0.9	4.5		
		J/SST204	0.2	3		
$I_{GSS}$	Gate Reverse Current	-2		-100	pA	$V_{GS} = -20V, V_{DS} = 0V$
$I_G$	Gate Operating Current		-2			$V_{DG} = 10V, I_D = 0.1mA$
$I_{D(off)}$	Drain Cutoff Current		2			$V_{DS} = 15V, V_{GS} = -5V$
$g_{fs}$	Forward Transconductance	J/SST201, 204	0.5		mS	$V_{DS} = 15V, V_{GS} = 0V, f = 1kHz$
		J/SST202	1			
$C_{iss}$	Input Capacitance		4.5		pF	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$
$C_{rss}$	Reverse Transfer Capacitance		1.3			
$e_n$	Noise Voltage		6		nV/ $\sqrt{Hz}$	$V_{DS} = 10V, V_{GS} = 0V, f = 1kHz$

## TO-92



## SOT-23



1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
2. Pulse Test:  $PW \leq 300\mu s$ , Duty Cycle  $\leq 3\%$

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